

# **Device Modeling Report**

COMPONENTS:

DIODE/ GENERAL PURPOSE RECTIFIER / STANDARD

PART NUMBER: RHRP30120

MANUFACTURER: INTERSIL

REMARK: TC=80C

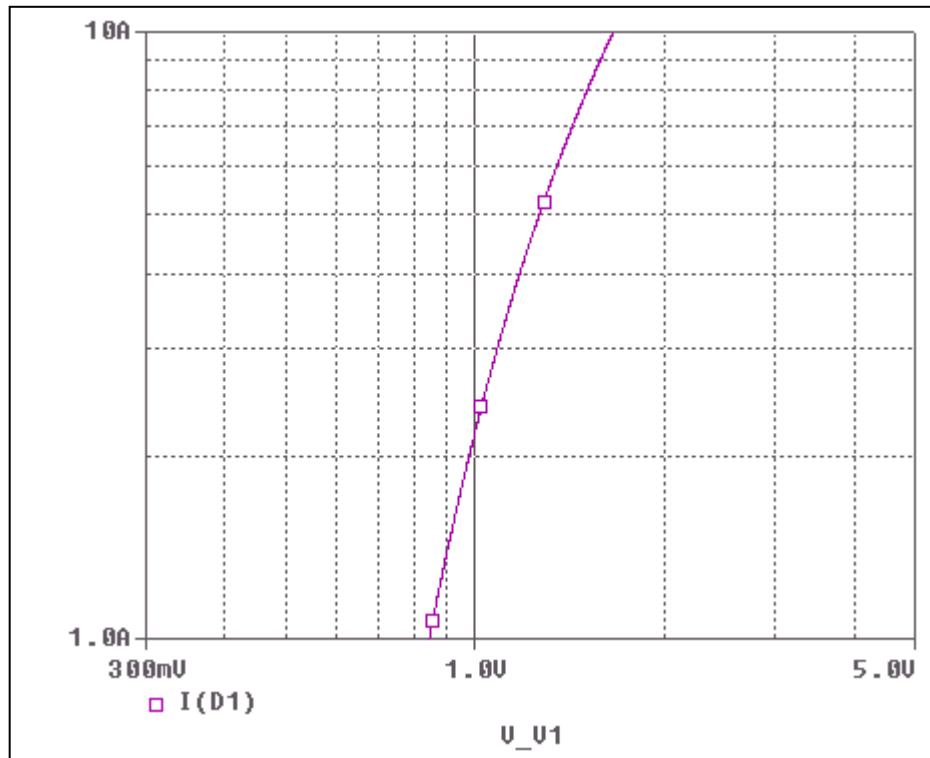


**Bee Technologies Inc.**

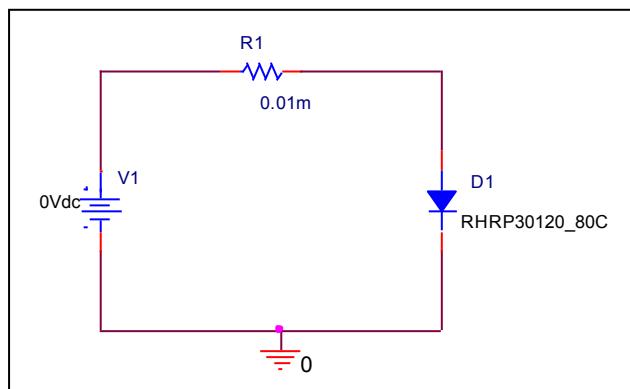
PSpice model parameter	Model description
IS	Saturation Current
N	Emission Coefficient
RS	Series Resistance
IKF	High-injection Knee Current
CJO	Zero-bias Junction Capacitance
M	Junction Grading Coefficient
VJ	Junction Potential
ISR	Recombination Current Saturation Value
BV	Reverse Breakdown Voltage(a positive value)
IBV	Reverse Breakdown Current(a positive value)
TT	Transit Time
EG	Energy-band Gap

## Forward Current Characteristic

Circuit Simulation Result

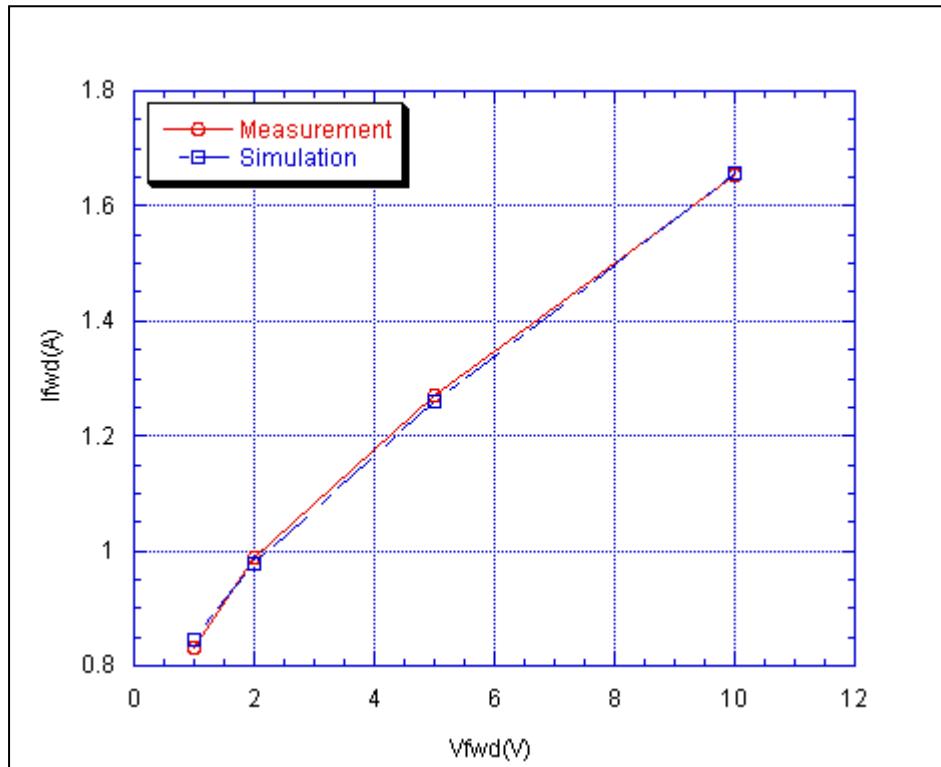


Evaluation Circuit



## Comparison Graph

Circuit Simulation Result

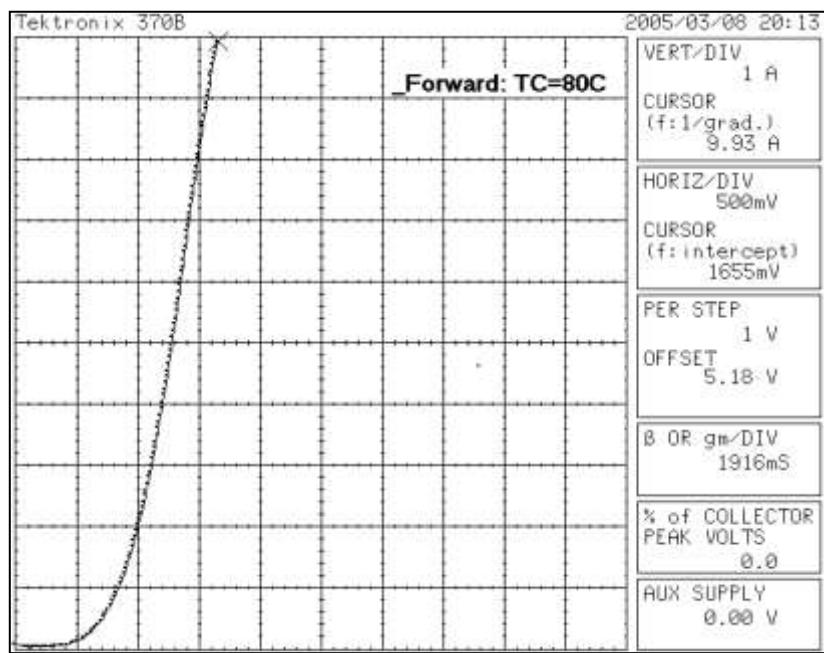


Simulation Result

$I_{fwd}$ (A)	$V_{fwd}$ (V) Measurement	$V_{fwd}$ (V) Simulation	%Error
1	0.830	0.845	-1.86
2	0.990	0.978	1.18
5	1.270	1.261	0.71
10	1.655	1.658	-0.18

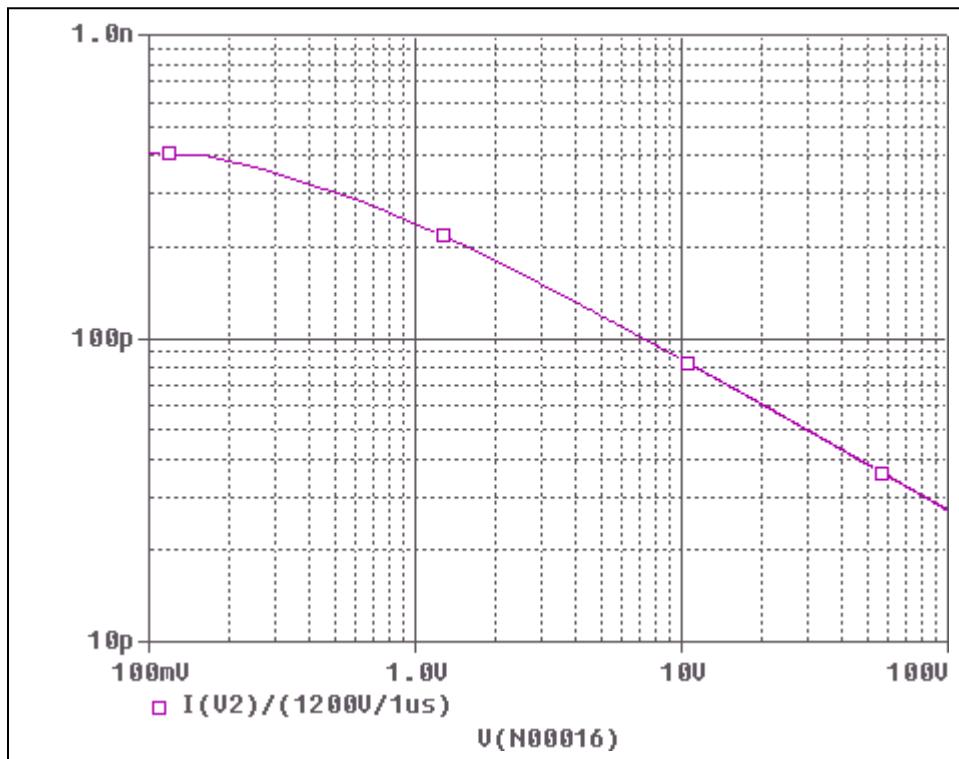
## Forward Current Characteristic

## Reference

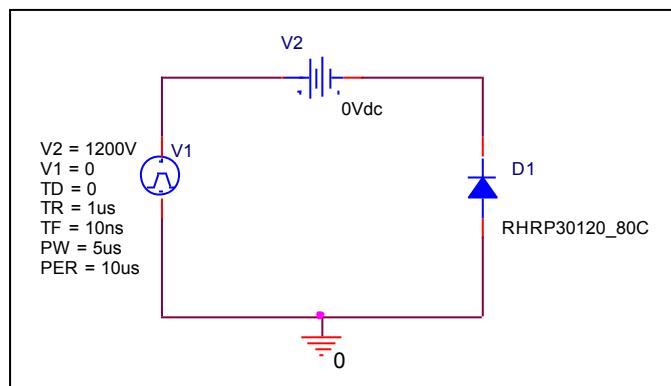


## Capacitance Characteristic

### Circuit Simulation Result

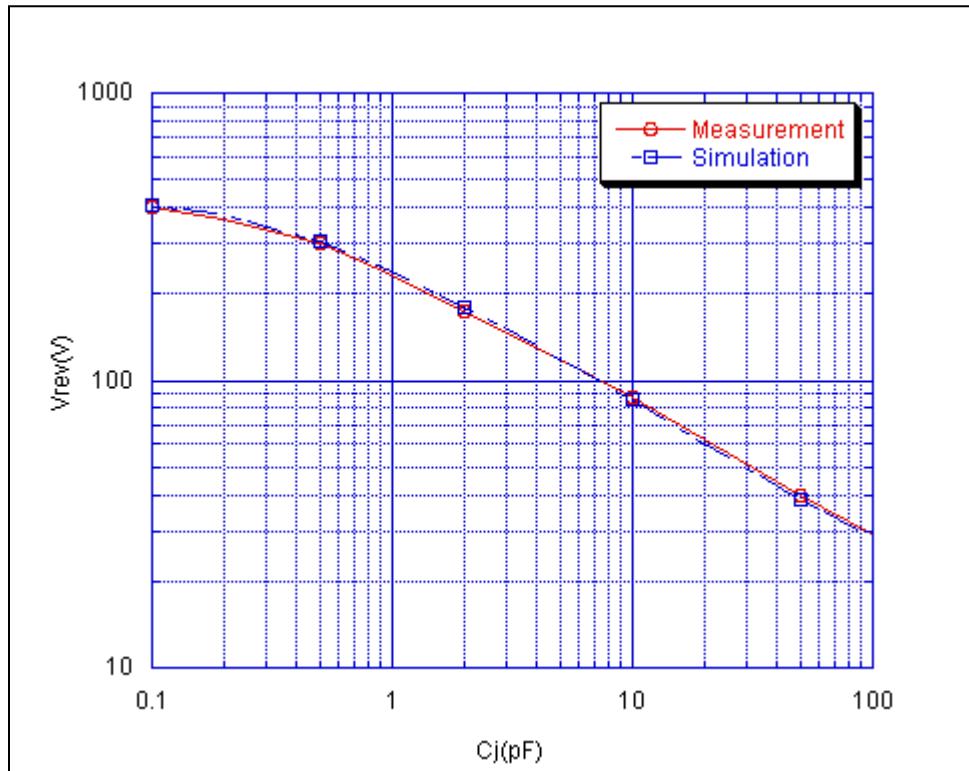


### Evaluation Circuit



## Comparison Graph

Circuit Simulation Result

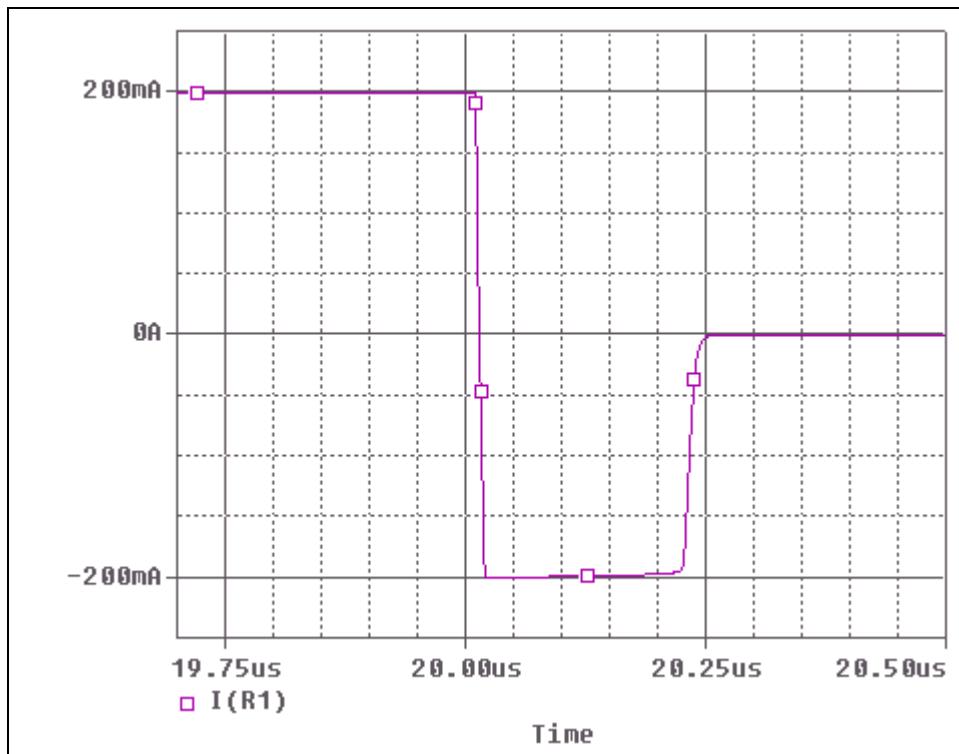


Simulation Result

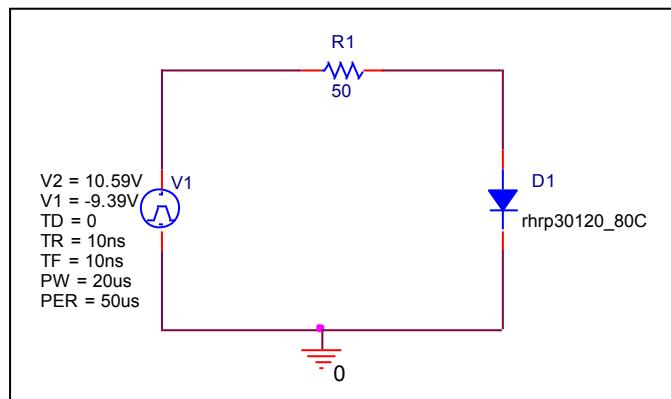
$V_{rev}$ (V)	$C_j$ (pF) Measurement	$C_j$ (pF) Simulation	%Error
0	449.000	449.000	0.00
0.1	401.000	410.500	-2.37
0.2	366.000	374.200	-2.24
0.5	302.000	303.600	-0.53
1	231.000	238.778	-3.37
2	174.000	180.283	-3.61
5	118.000	119.055	-0.89
10	87.000	85.276	1.98
20	62.000	60.505	2.41
50	40.000	38.597	3.51
100	29.000	28.000	3.45

## Reverse Recovery Characteristic

### Circuit Simulation Result



### Evaluation Circuit

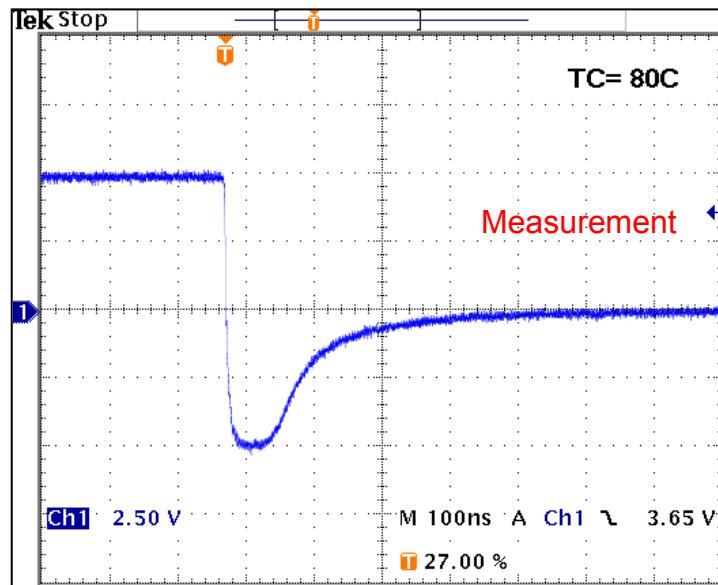


### Compare Measurement vs. Simulation

	Measurement		Simulation		%Error
trr	226.00	ns	225.73	ns	- 0.115

## Reverse Recovery Characteristic

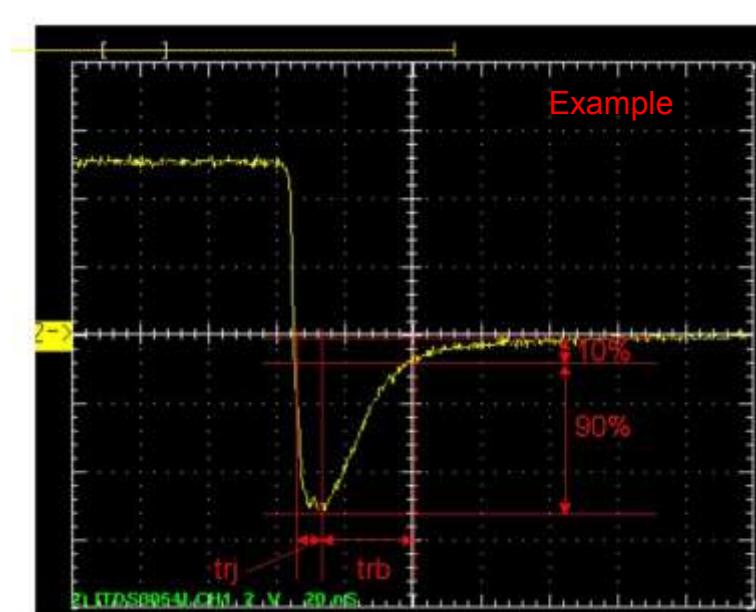
## Reference



Trj =52 (ns)

Trb=174 (ns)

Conditions: Ifwd=Irev=0.2(A), RI=50



Relation between trj and trb